



## SOT-323 Plastic-Encapsulate Diodes

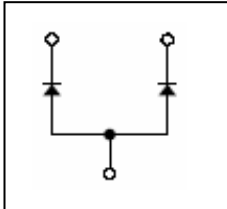
### DAP202U

#### SWITCHING DIODE

#### FEATURES:

- Four types of packaging are available
- High speed. ( $t_{rr}=1.5ns$  Typ.)
- Suitable for high packing density layout
- High reliability.
- **Pb-Free package is available**  
RoHS product for packing code suffix "G"  
Halogen free product for packing code suffix "H"
- **Moisture Sensitivity Level 1**

#### SOT-323



MARKING: P

#### Maximum Ratings @ $T_A=25^\circ C$

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	80	V
DC reverse voltage	$V_R$	80	V
Maximum (peak) forward current	$I_{FM}$	300	mA
Average forward current	$I_O$	100	mA
Power dissipation	$P_D$	200	mW
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55-150	$^\circ C$

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	$I_R$	$V_R=70V$		0.1	$\mu A$
Forward voltage	$V_F$	$I_F=100mA$		1.2	V
Diode capacitance	$C_D$	$V_R=6V, f=1MHz$		3.5	pF
Reverse recovery time	$t_{rr}$	$V_R=6V, I_F=5mA$		4	ns

**Typical Characteristics**

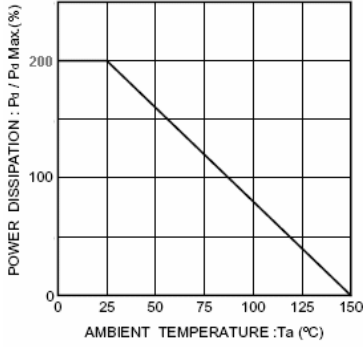


Fig.1 Power attenuation curve

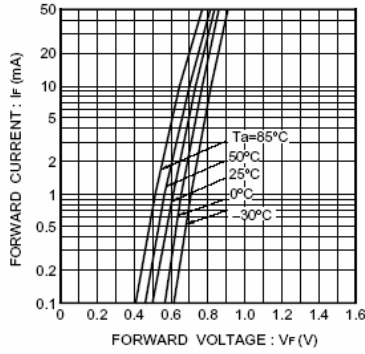


Fig.2 Forward characteristics (P Type)

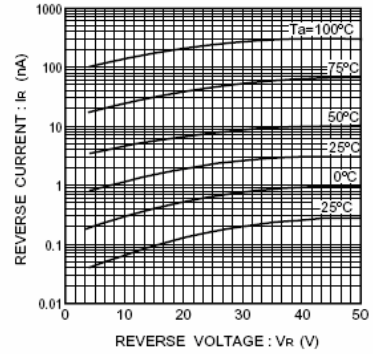


Fig.3 Reverse characteristics (P Type)

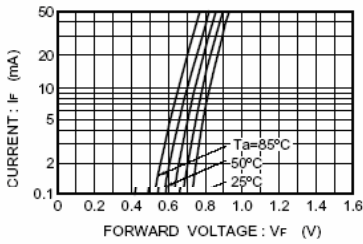


Fig.4 Forward characteristics (N Type)

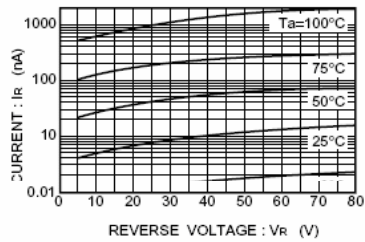


Fig.5 Reverse characteristics (N Type)

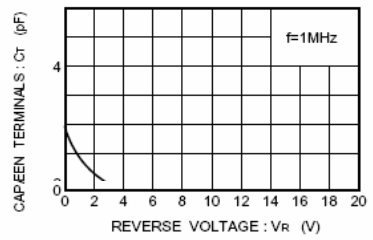


Fig.6 Capacitance between terminals characteristics

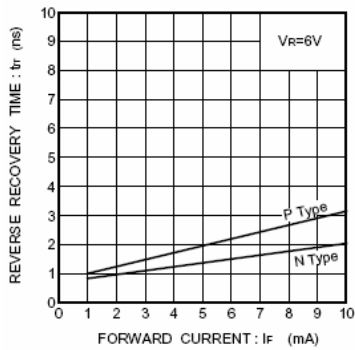


Fig.7 Reverse recovery time

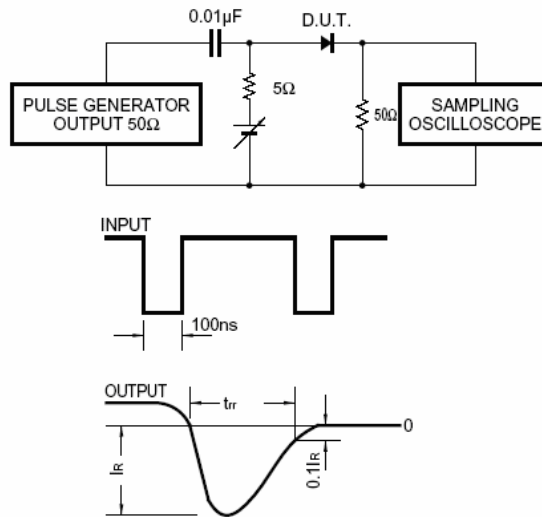
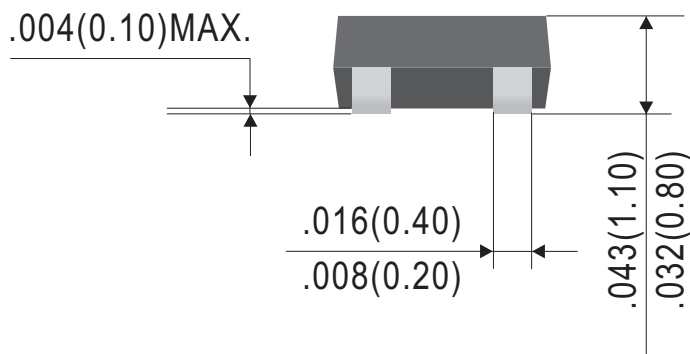
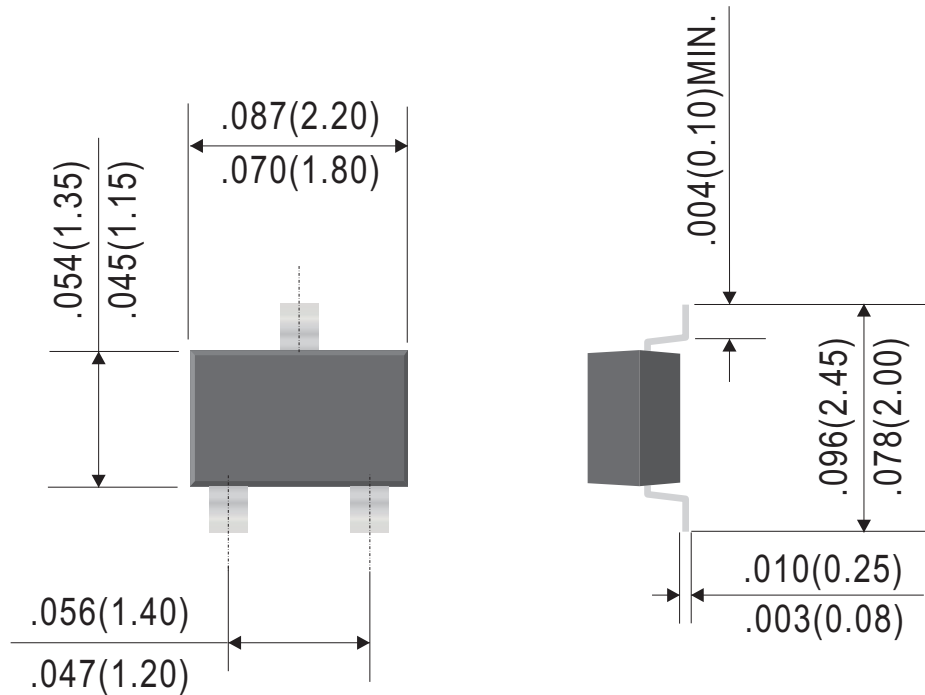


Fig.8 Reverse recovery time ( $t_r$ ) measurement circuit



# Outline Drawing

# SOT-323



Dimensions in inches and (millimeters)